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To: Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572  
20 McIntosh Drive  
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 09/531,403 03/20/00

Ma-Chi Chiang, Hsien-Chin Lin,  
Liaw-Ren Shih

A NOVEL METHOD FOR IMPROVING HOT  
CARRIER LIFETIME VIA A NITROGEN  
IMPLANTATION PROCEDURE PERFORMED  
BEFORE OR AFTER A TEOS LINER  
DEPOSITION

Grp. Art Unit:

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56. Copies of each document is included herewith.

U.S. Patent 5,994,175 to Gardner et al., "High Performance  
MOSFET with Low Resistance Design", discloses a N I/I before  
the LDD.

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U.S. Patent 5,972,783 to Arai et al., "Method for Fabricating a Semiconductor Device Having a Nitrogen Diffusion Layer", teaches an angled N<sub>2</sub> and LDD I/I.

U.S. Patent 5,885,877 to Gardner et al., "Composite Gate Electrode Incorporating Dopant Diffusion-Retarding Barrier Layer Adjacent to Underlying Gate Dielectric", discloses a LDD process with a N<sub>2</sub> anneal.

U.S. Patent 5,920,782 to Shih et al., "Method for Improving Hot Carrier Degradation", discloses a N<sub>2</sub> I/I to improve hot carrier degradation.

Sincerely,



Stephen B. Ackerman,  
Reg. No. 37761